## 1 Characteristics

Table 2: Absolute maximum ratings (limiting values)

Symbol	Parame	Value	Unit		
I <sub>T(RMS)</sub>	RMS on-state current (full sine wave	e)	T <sub>c</sub> = 124 °C	12	А
	Non repetitive surge peak on-state o	t <sub>p</sub> = 16.7 ms	95	A	
Ітѕм	T <sub>j</sub> initial = 25 °C	t <sub>p</sub> = 20 ms	90		
l²t	I <sup>2</sup> t value for fusing		T <sub>j</sub> initial = 25 °C	54	A <sup>2</sup> s
dl/dt	Critical rate of rise of on-state currer $I_G = 2 \times I_{GT}$ , tr $\leq 100 \text{ ns}$	100	A/µs		
λ/Λ/	Departitive peak off state voltage	T <sub>j</sub> = 150 °C	600	V	
Vdrm/Vrrm	Repetitive peak off-state voltage	spellive peak on-state voltage		800	V
Vdsm/Vrsm	Non Repetitive peak off-state voltag	$t_p = 10 \text{ ms}$	900	V	
I <sub>GM</sub>	Peak gate current	t <sub>p</sub> = 20 μs	T <sub>j</sub> = 150 °C	4	А
P <sub>G(AV)</sub>	Average gate power dissipation	1	W		
T <sub>stg</sub>	Storage junction temperature range	-40 to +150	°C		
Tj	Operating junction temperature rang	-40 to +150	°C		

Table 3: Electrical characteristics (T<sub>j</sub> = 25 °C, unless otherwise specified)

Symbol	Test conditions	Quadrants; Tj		Value	Unit
1	$V_D$ = 12 V, R <sub>L</sub> = 33 $\Omega$	-    -	Min.	1.75	mA
I <sub>GT</sub>	$V_D = 12 \text{ V}, \text{ R}_L = 33 \Omega$	-    -	Max.	35	mA
Vgt	$V_D$ = 12 V, R <sub>L</sub> = 33 $\Omega$	-    -	Max.	1.3	V
Vgd	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 150 ^\circ\text{C}$	-    -	Min.	0.2	V
١L	$I_G = 1.2 \text{ x } I_{GT}$	1 - 111	Max.	60	mA
IL.	IG = 1.2 x IGT	II	Max.	80	mA
IH <sup>(1)</sup>	I⊤ = 500 mA, gate open	Max.	40	mA	
dV/dt (1)	V <sub>D</sub> = 536 V, gate open	T <sub>j</sub> = 125 °C	Min.	2000	V/µs
	V <sub>D</sub> = 402 V, gate open	T <sub>j</sub> = 150 °C	Min.	1000	V/µs
(dl/dt)o(1)	Without anyther (d)/(dt) > 20 )//up	T <sub>j</sub> = 125 °C	Min.	12	A/ms
(dl/dt)c <sup>(1)</sup>	Without snubber, (dV/dt)c > 20 V/µs	T <sub>j</sub> = 150 °C	Min.	6	A/ms

### Notes:

 $^{(1)}\mbox{For both polarities of A2 referenced to A1.}$ 



## Characteristics

				enaraet			
	Table 4: Static characteristics						
Symbol	Test conditions	Tj		Value	Unit		
Vtm <sup>(1)</sup>	$I_T = 17 \text{ A}, t_p = 380 \ \mu s$	25 °C	Max.	1.6	V		
Vто <sup>(1)</sup>	Threshold on-state voltage	150 °C	Max.	0.85	V		
R <sub>D</sub> <sup>(1)</sup>	Dynamic resistance	150 °C	Max.	50	mΩ		
	V <sub>DRM</sub> = V <sub>RRM</sub> = 800 V	25 °C	Max.	5	μA		
Idrm/Irrm	$v_{\text{DRM}} = v_{\text{RRM}} = 800$ v	125°C	ividX.	1	mA		
	$V_{DRM} = V_{RRM} = 600 \text{ V}$	150 °C	Max.	3.1	mA		

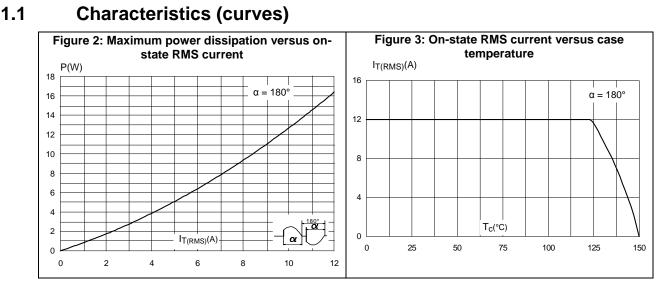
### Notes:

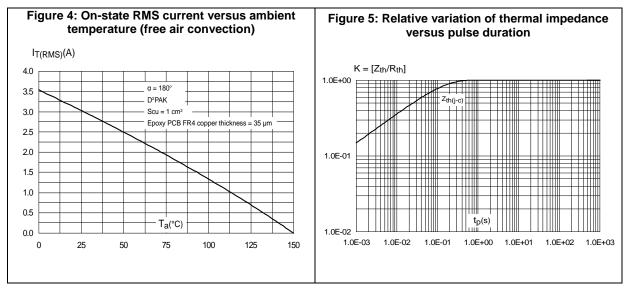
 $^{(1)}\mbox{For both polarities of A2 referenced to A1.}$ 

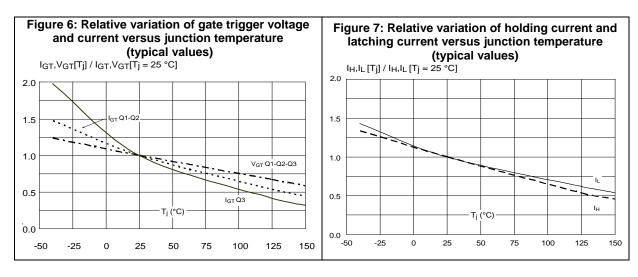
### Table 5: Thermal resistance

Symbol	Parameter	Value	Unit		
R <sub>th(j-c)</sub>	Junction to case (AC)	D²PAK	Max.	1.6	°C/W









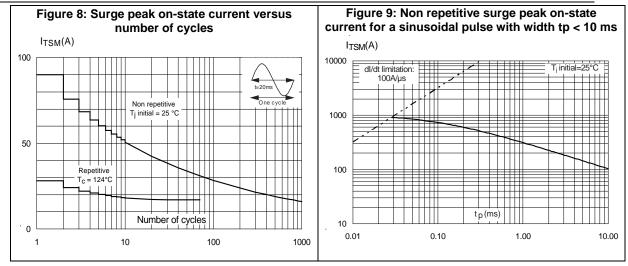
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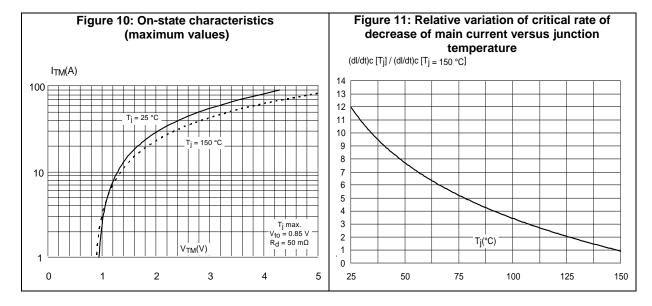
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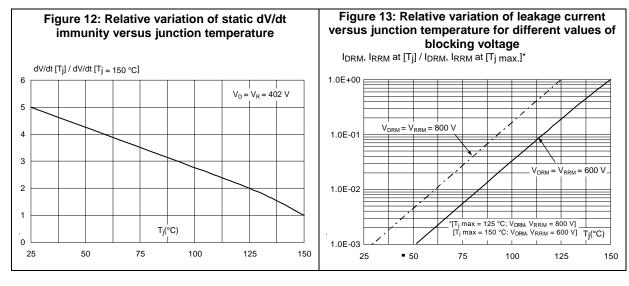


### T1235T-8G

### **Characteristics**







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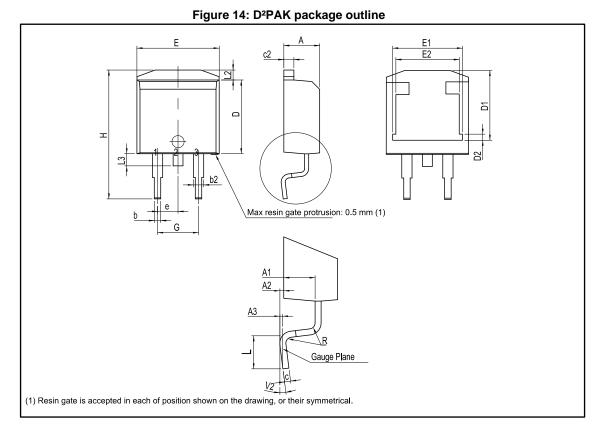
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## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

- ECOPACK<sup>®</sup>2 compliant
- Lead-free package leads finishing
- Molding compound resin is halogen-free and meets UL standard level V0

## 2.1 D<sup>2</sup>PAK package information



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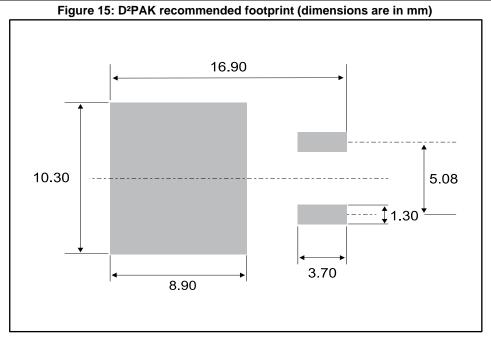
## Package information

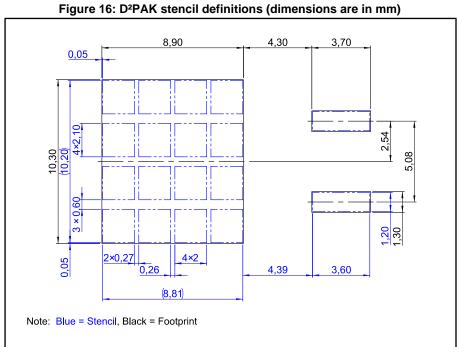
	Table 6: D <sup>2</sup> PAK package mechanical data							
	Dimensions							
Ref.		Millimeters		Inches <sup>(1)</sup>				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
А	4.30		4.60	0.1693		0.1811		
A1	2.49		2.69	0.0980		0.1059		
A2	0.03		0.23	0.0012		0.0091		
A3		0.25			0.0098			
b	0.70		0.93	0.0276		0.0366		
b2	1.25		1.7	0.0492		0.0669		
С	0.45		0.60	0.0177		0.0236		
c2	1.21		1.36	0.0476		0.0535		
D	8.95		9.35	0.3524		0.3681		
D1	7.50		8.00	0.2953		0.3150		
D2	1.30		1.70	0.0512		0.0669		
е	2.54			0.1				
E	10.00		10.28	0.3937		0.4047		
E1	8.30		8.70	0.3268		0.3425		
E2	6.85		7.25	0.2697		0.2854		
G	4.88		5.28	0.1921		0.2079		
Н	15		15.85	0.5906		0.6240		
L	1.78		2.28	0.0701		0.0898		
L2	1.27		1.40	0.0500		0.0551		
L3	1.40		1.75	0.0551		0.0689		
R		0.40			0.0157			
V2	0°		8°	0°		8°		

## Notes:

 $\ensuremath{^{(1)}}\xspace$  Dimensions in inches are given for reference only







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# **3** Ordering information

Figure 17: 0	Drdering	information	scheme

Snubberless™ TRIAC			
RMS current			
12 = 12  A			
I <sub>GT</sub> current			
35 = 35 mA			
Specific application			
T = increased (dl/dt) and dV/d	It producing reduc	ced I <sub>TSM</sub>	
Voltage			
8 = 800 V			
Package			
G = D <sup>2</sup> PAK			
Packing			
Blank = Tube			

Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
T1235T-8G-TR	T4005T 00	D²PAK	1.00 ~	1000	Tape and reel
T1235T-8G	T1235T-8G		1.38 g	50	Tube

# 4 Revision history

## Table 8: Document revision history

Date	Revision	Changes
19-Dec-2017	1	Initial release.



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